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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/596,249	06/06/2006	Frederick William Buehrer	FIS920030120US1	4225
45828 7590 04/09/2009 WHITHAM, CURTIS & CHRISTOFFERSON, P.C. 11491 SUNSET HILLS ROAD, SUITE 340 RESTON, VA 20190				
EXAMINER				
SARKAR, ASOK K				
ART UNIT		PAPER NUMBER		
2891				
MAIL DATE		DELIVERY MODE		
04/09/2009		PAPER		

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Office Action Summary**Application No.**

10/596,249

Applicant(s)

BUEHRER ET AL.

Examiner

Asok K. Sarkar

Art Unit

2891

Period for Reply -- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 06 June 2006.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-20 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-20 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 06 June 2006 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (PTO-893)
- 4) ☐ Interview Summary (PTO-413)
- 5) ☐ Notice of Informal Patent Application
- 6) ☐ Other: _____
- Paper No(s)/Mail Date 6/6/06 and 3/25/08

DETAILED ACTION

Election/Restrictions

1. Applicant's explanation regarding the validity of the election/restriction was found to be persuasive. Therefore the restriction requirement was vacated. All claims were examined together.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

3. Claims 1 – 6, 14 – 18 and 20 are rejected under 35 U.S.C. 102(b) as being anticipated by Guldi, US 5,525,529.

Regarding claim 1, Guldi teaches a method for modifying a diffusions rate of an impurity implanted in a semiconductor material including steps of

- defining a boundary with a structure on a surface of said semiconductor material with reference to Fig. 3;
- applying a stressed film 58 over said structure and said surface at said boundary with reference to Fig. 3; and
- annealing said semiconductor material to activate said impurities in column 6, lines 31 – 35 and in column 8, lines 1 – 12.

Regarding claim 2, Guldi teaches the structure on said surface of said semiconductor material is a gate structure of a field effect transistor with reference to Fig. 5.

Regarding claim 3, Guldi teaches the boundary is defined by a sidewall of said gate structure with reference to Fig. 5.

Regarding claims 4 and 5, Guldi teaches the sidewall is an offset spacer and said sidewall is a source/drain spacer with reference to Fig. 5.

Regarding claim 6, Guldi teaches the boundary is defined by a gate electrode of said gate structure with reference to Fig. 5.

Regarding claim 14, Guldi teaches an intermediate structure for formation of a semiconductor device, said intermediate structure comprising

- a body of semiconductor material including respective regions implanted with boron and arsenic impurities,
- a structure on a surface on said body of semiconductor material and forming a boundary, and
- a stressed film extending over said structure and said boundary, wherein when said intermediate structure is annealed to activate said boron and arsenic impurities, a diffusion rate of said boron impurities is modified as was described earlier in rejecting claim 1 with references to Figs. 1 – 5 in columns 5 – 8 and especially in column 8, lines 1 – 12.

Regarding claims 15 – 18, Guldi teaches the limitations of these claims as were described earlier in rejecting claims 2 – 5.

Regarding claim 20, Guldi teaches a pFET including

- a source/drain region formed by implantation with boron, and
- an extension region formed by implantation with boron, wherein a boron concentration profile of said extension in a lateral direction differs from a boron concentration in a vertical direction with reference to Figs 1 – 3 and 5 in discussions in between columns 5 – 8 as was described earlier in rejecting claims 1 and 14.

4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

5. The factual inquiries set forth in *Graham v. John Deere Co.*, 383 U.S. 1, 148 USPQ 459 (1966), that are applied for establishing a background for determining obviousness under 35 U.S.C. 103(a) are summarized as follows:

1. Determining the scope and contents of the prior art.
2. Ascertaining the differences between the prior art and the claims at issue.
3. Resolving the level of ordinary skill in the pertinent art.
4. Considering objective evidence present in the application indicating obviousness or nonobviousness.

6. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was

not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

7. Claims 7 – 12 and 19 are rejected under 35 U.S.C. 103(a) as being unpatentable over Guldi, US 5,525,529 in view of Ahmad, US 6,159,813.

Regarding claim 7, Guldi teaches the steps of implanting extension impurities, implanting source/drain impurities, but fails to teach implanting halo impurities.

Ahmad teaches implanting halo impurities with reference to Fig. 9 for the benefit of optimizing the concentration of p –type charge carriers in column 4, lines 15 – 20.

Therefore, it would have been obvious to one with ordinary skill in the art at the time of the invention to modify Guldi and implant halo impurities for the benefit of optimizing the concentration of p –type charge carriers as taught by Ahmad in column 4, lines 15 – 20.

Regarding claim 8, Guldi in view of Ahmad teaches a plurality of said structures are provided on said surface of said semiconductor material, but fails to teach the step of removing said stressed film from a selected said structure prior to said annealing step,

Therefore, it would have been obvious to one with ordinary skill in the art at the time of the invention to modify Guldi in view of Ahmad and remove said stressed film from a selected said structure prior to said annealing step so that the gate top and the source and drain regions can be silicided for lowering resistivity.

Regarding claim 9, Guldi teaches plurality of structures include gate structures of pFETs and nFETs with reference to Figs. 1 – 3.

Regarding claims 10 – 12, Guldi teaches these limitations as were described earlier in rejecting claims 3 – 5.

Regarding claim 19, Guldi teaches an integrated circuit comprising a pFET, and an nFET, but fails to teach wherein a boron diffusion concentration profile from extension implants in said pFET corresponds to a lower boron diffusion rate than a boron diffusion rate corresponding to a boron diffusion concentration profile from a boron halo implant in said nFET.

Ahmad teaches implanting halo impurities with reference to Fig. 9 for the benefit of optimizing the concentration of p –type charge carriers in column 4, lines 15 – 20.

Therefore, the net effect of annealing after the halo implant will produce a boron diffusion concentration profile from extension implants in said pFET corresponds to a lower boron diffusion rate than a boron diffusion rate corresponding to a boron diffusion concentration profile from a boron halo implant in said nFET. due to the stress effect of the silicon nitride film in Guldi's device.

8. Claim 13 is rejected under 35 U.S.C. 103(a) as being unpatentable over Guldi, US 5,525,529 in view of Yeo, US 6,882,025.

Guldi teaches the stressed film, but fails to teach the film is a tensile film.

Yeo teaches the deposited silicon nitride film is associated with intrinsic tensile stress in column 4, lines 59 – 61.

Therefore, it would have been obvious to one with ordinary skill in the art at the time of the invention that the silicon nitride film is associated with intrinsic tensile stress as taught by Yeo in column 4, lines 59 – 61.

Conclusion

9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Asok K. Sarkar whose telephone number is 571 272 1970. The examiner can normally be reached on Monday - Friday (9 AM- 6 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Sue A. Purvis can be reached on 571 272 1236. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

10. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Asok K. Sarkar/
Primary Examiner, Art Unit 2891
March 31, 2009